

1SS355

Silicon Epitaxial Planar Switching Diode

Features

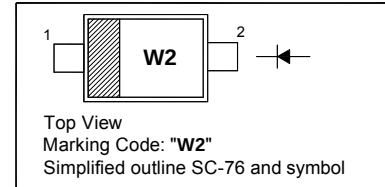
- Small plastic package suitable for surface mounted design
- High reliability with high surge current handling capability

Applications

- High speed switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

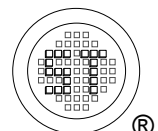


Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

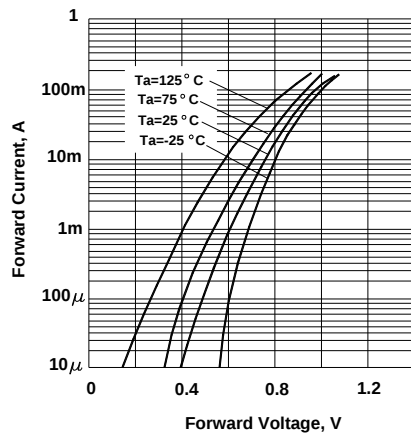
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	90	V
Reverse Voltage	V_R	80	V
Average Rectified Forward Current	$I_{F(AV)}$	100	mA
Peak Forward Current	I_{FM}	225	mA
Surge Forward Current (1 s)	I_{FSM}	500	mA
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

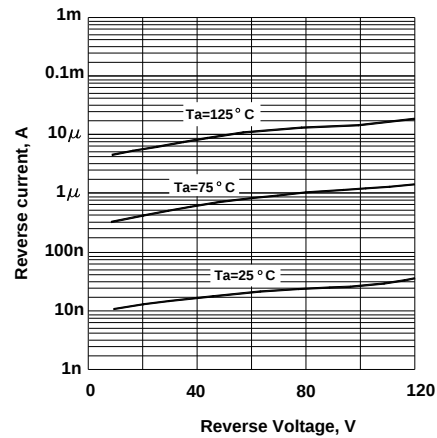
Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	V_F	1.2	V
Reverse Current at $V_R = 80\text{ V}$	I_R	0.1	μA
Capacitance between Terminals at $V_R = 0.5\text{ V}$, $f = 1\text{ MHz}$	C_T	3	pF
Reverse Recovery Time at $V_R = 6\text{ V}$, $I_F = 10\text{ mA}$, $R_L = 100\ \Omega$	t_{rr}	4	ns



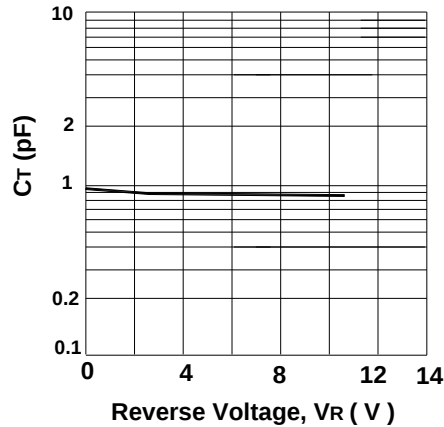
Forward Characteristics



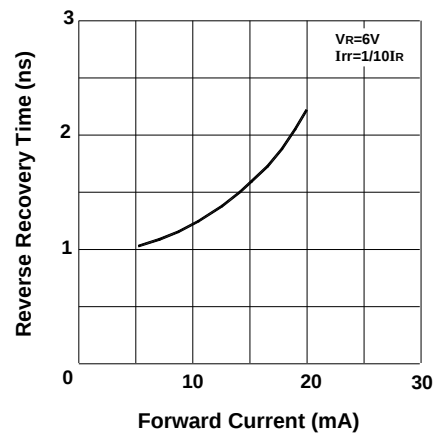
Reverse Characteristics



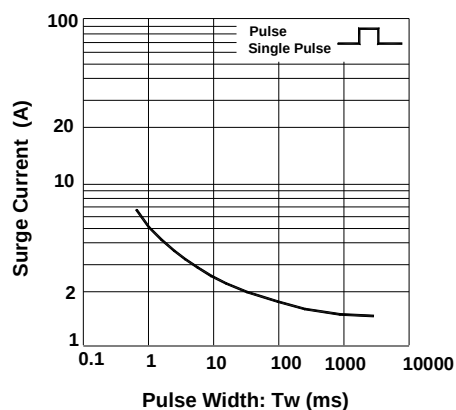
Capacitance between terminals characteristics



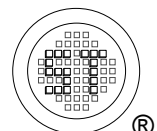
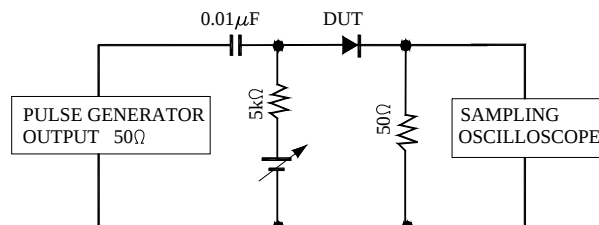
Reverse Recovery Time Characteristics



Surge Current Characteristics



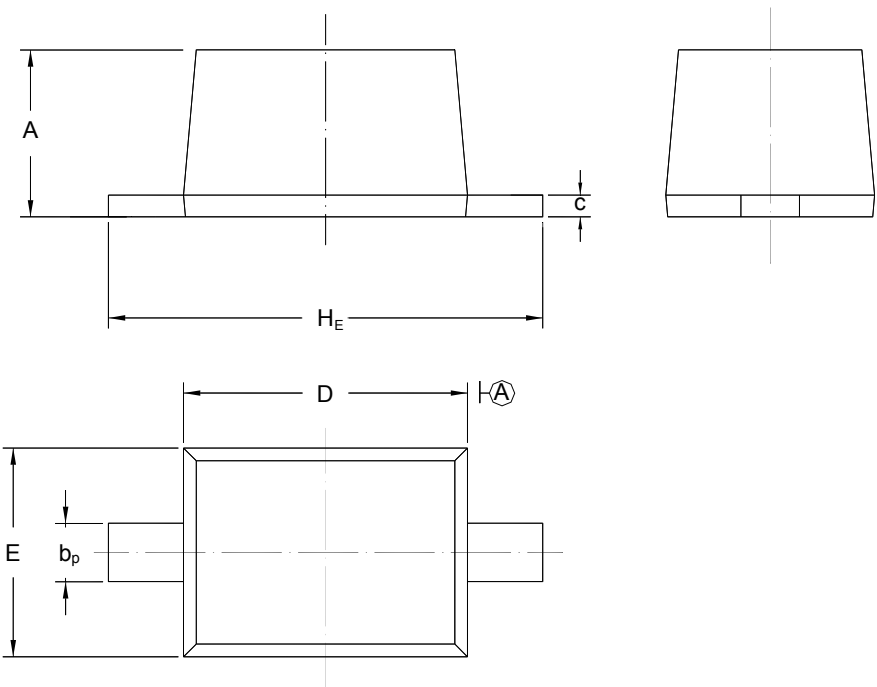
Reverse Recovery Time Measurement Circuit



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SC-76



UNIT	A	b_p	C	D	E	H_E
mm	1.10 0.80	0.40 0.25	0.15 0.10	1.80 1.60	1.35 1.15	2.80 2.30

